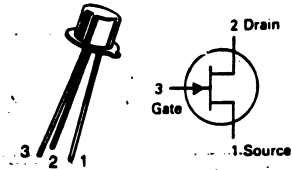


**2N4391
 thru
 2N4393**

TO-18



**JFETs
 SWITCHING**

— N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	40	Vdc
Drain-Gate Voltage	V _{DG}	40	Vdc
Gate-Source Voltage	V _{GS}	40	Vdc
Forward Gate Current	I _{GF}	50	mAdc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.8 10	Watts mW/°C
Operating Junction Temperature Range	T _J	-65 to +175	°C
Storage Temperature Range	T _{stg}	-65 to +175	°C

*** ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)**

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage (I _G = 1.0 μAdc, V _{DS} = 0)	V _{(BR)GSS} ✓	40	—	Vdc
Gate Reverse Current (V _{GS} = 20 Vdc, V _{DS} = 0) (V _{GS} = 20 Vdc, V _{DS} = 0, T _A = 150°C)	I _{GSS} ✓	— —	0.1 0.2	nAdc μAdc
Gate-Source Voltage (V _{DS} = 20 Vdc, I _D = 1.0 nAdc)	V _{GS}	-4.0 -2.0 -0.5	-10 -5.0 -3.0	Vdc
Gate-Source Forward Voltage (I _G = 1.0 mAdc, V _{DS} = 0)	V _{GS(f)} ✓	—	1.0	Vdc
Drain-Cutoff Current (V _{DS} = 20 Vdc, V _{GS} = 12 Vdc) (V _{DS} = 20 Vdc, V _{GS} = 7.0 Vdc) (V _{DS} = 20 Vdc, V _{GS} = 5.0 Vdc) (V _{DS} = 20 Vdc, V _{GS} = 2 Vdc, T _A = 150°C) (V _{DS} = 20 Vdc, V _{GS} = 7.0 Vdc, T _A = 150°C) (V _{DS} = 20 Vdc, V _{GS} = 5.0 Vdc, T _A = 150°C)	I _{D(off)} ✓	— — — — — —	0.1 0.1 0.1 0.2 0.2 0.2	nAdc μAdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current(1) (V _{DS} = 20 Vdc, V _{GS} = 0)	I _{DSS} ✓	50 25 5.0	150 75 30	mAdc
Drain-Source On-Voltage (I _D = 12 mAdc, V _{GS} = 0) (I _D = 6.0 mAdc, V _{GS} = 0) (I _D = 3.0 mAdc, V _{GS} = 0)	V _{DS(on)} ✓	— — —	0.4 0.4 0.4	Vdc
Static Drain-Source On Resistance (I _D = 1.0 mAdc, V _{GS} = 0)	r _{DS(on)}	— — —	30 60 100	Ohms
SMALL-SIGNAL CHARACTERISTICS				
Drain-Source "ON" Resistance (V _{GS} = 0, I _D = 0, f = 1.0 kHz)	r _{ds(on)}	— — —	30 60 100	Ohms



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2N4391 thru 2N4393

*ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Input Capacitance ($V_{DS} = 20 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ MHz}$)	C_{iss}	—	14	pF
Reverse Transfer Capacitance ($V_{DS} = 0$, $V_{GS} = 12 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	C_{rss}	—	3.5	pF
($V_{DS} = 0$, $V_{GS} = 7.0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)		—	3.5	
($V_{DS} = 0$, $V_{GS} = 5.0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)		—	3.5	

SWITCHING CHARACTERISTICS

Rise Time ($I_{D(on)} = 12 \text{ mAdc}$)	2N4391	t_r	—	5.0	ns
($I_{D(on)} = 6.0 \text{ mAdc}$)	2N4392		—	5.0	
($I_{D(on)} = 3.0 \text{ mAdc}$)	2N4393		—	5.0	
Fall Time ($V_{GS(off)} = 12 \text{ Vdc}$)	2N4391	t_f	—	15	ns
($V_{GS(off)} = 7.0 \text{ Vdc}$)	2N4392		—	20	
($V_{GS(off)} = 5.0 \text{ Vdc}$)	2N4393		—	30	
Turn-On Time ($I_{D(on)} = 12 \text{ mAdc}$)	2N4391	t_{on}	—	15	ns
($I_{D(on)} = 6.0 \text{ mAdc}$)	2N4392		—	15	
($I_{D(on)} = 3.0 \text{ mAdc}$)	2N4393		—	15	
Turn-Off Time ($V_{GS(off)} = 12 \text{ Vdc}$)	2N4391	t_{off}	—	20	ns
($V_{GS(off)} = 7.0 \text{ Vdc}$)	2N4392		—	35	
($V_{GS(off)} = 5.0 \text{ Vdc}$)	2N4393		—	50	

(1) Pulse Test: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle $\leq 1.0\%$.
 *In addition to JEDEC Registered Data.



Quality Semi-Conductors